Erratum: Study of GaN thin layers subjected to high-temperature rapid thermal annealing [Semiconductors 32, No. 10, 1048 (October 1998)]

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The Editorial Board of ''Fizika i Tekhnika Poluprovodnikov'' informs of the correction that should be made in this article. On page 1048, Section 2, the first sentence of the second paragraph, should read as follows:

''RHTA was performed in a quartz reactor at a temperature of 1000 C for 30 s in a stream of N_2 or Ar.''

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